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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









SD1433

RF POWER BIPOLAR TRANSISTORS UHF MOBILE APPLICATIONS

FEATURES SUMMARY

- 470 MHz
- 12.5 VOLTS
- CLASS C
- EFFICIENCY 60%
- COMMON EMITTER
- P_{OUT} = 10 W MIN. WITH 8.0 dB GAIN

DESCRIPTION

The SD1433 is a Class C epitaxial silicon NPN planar transistor designed for driver applications in the 450 - 512 MHz frequency range. This device uses an emitter ballasted geometry specifically designed for optimum stable power gain, maximum efficiency and infinite VSWR.



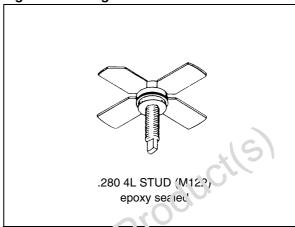


Figure 2. Pir Connection

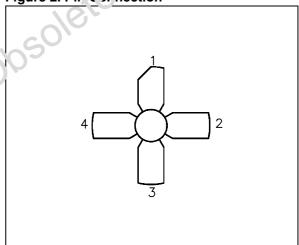


Table 1. Order Codes

Order Codes	Marking	Package	Packaging
SD1433	SD1433	M122	BLACK CARDBOARDS

REV. 2 May 2004

Table 2. Absolute Maximum Ratings (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	16	V
V _{CES}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	2.5	Α
P _{DISS}	Power Dissipation	58	W
TJ	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

Table 3. Thermal Data

Symbol	Parameter	Value	Unit
R _{TH(j-c)}	Junction-Case Thermal Resistance	3.0	°C/W

ELECTRICAL SPECIFICATIONS (TCASE = 25°C)

Table 4. Static

R _{TH(j-c)}	Junction-Case Thermal Resistance		3.0	- 1	°C/W
ELECTRICAL SPECIFICATIONS (T _{CASE} = 25°C) Table 4. Static					
Symbol	Symbol Test Conditions		Value		Unit
Symbol	rest conditions	Min.	Тур.	Max.	Oilit
BV _{CES}	I _C = 25 mA; V _{BE} = 0 V	36	_	_	V
BV _{CEO}	I _C = 20 mA; I _B = 0 mA	16	_	_	V
BV _{EBO}	I _E = 10 mA; I _C = 0 mA	4.0	_	_	V
I _{CES}	V _{CE} = 10 V; I _E = 0 mA	_	_	3	mA
I _{CBO}	V _{CB} = 15 V; I _E = 0 mA	_	_	2	mA
h _{FE}	V _{CE} = 5 V; I _C = 1 A	10	_	_	_

Table 5. Dynamic

Symbol	Test Conditions		Unit		
Symbol	rest conditions	Min.	Тур.	Max.	Oilit
Роит	$f = 470 \text{ MHz}; P_{IN} = 2.0 \text{ W}; V_{CE} = 12.5 \text{ V}$	10		_	W
G _P	f = 470 MHz; P _{OUT} = 10 W; V _{CE} = 12.5 V	7	_	_	dB
СОВ	f = 1 MHz; V _{CB} = 12.5 V	_	19		pF

TYPICAL PERFORMANCE

Figure 3. Power Output vs Power Input

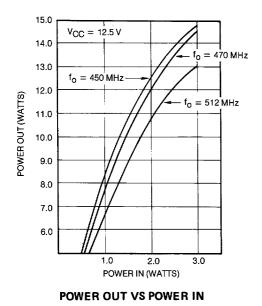
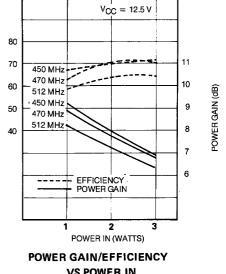


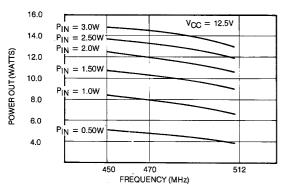
Figure 4. Power Gain & Efficiency vs Power Input



VS POWER IN

Obsolete

Figure 5. Power Output vs Frequency



POWER OUT VS FREQUENCY

IMPEDANCE DATA

Figure 6. Typical Input Impedance

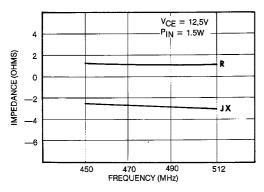


Figure 7. Typical Collector Load Impedance

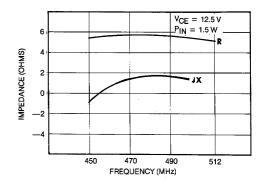


Table 6. Impedance Data

Table 6. Impedance Data		Producile
FREQ.	Z _{IN} (Ω)	Z _{CL} (Ω)
470 MHz	1.5 – j 2.7	5.7 + j 1.5
osoleite Produ		

TEST CIRCUIT

Figure 8. Test Circuit

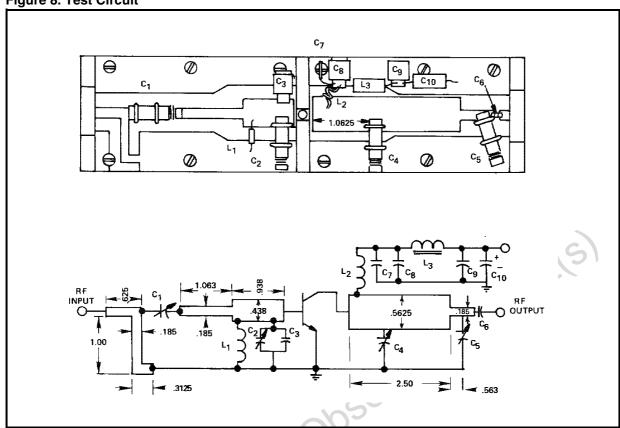


Table 7. Test Circuit

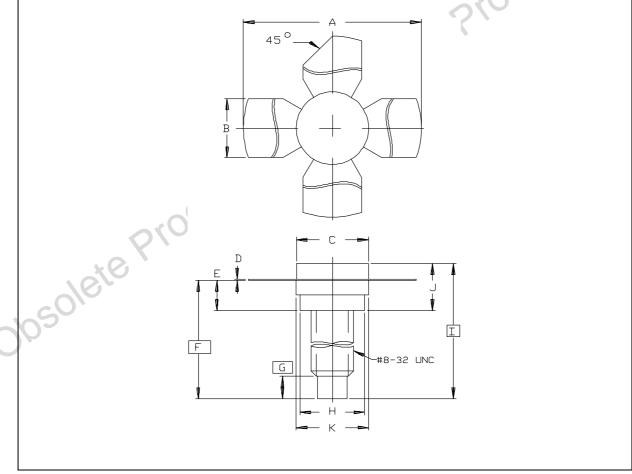
C1, C2:	0.8pF Voltronics		
C3:	18pF Chip Capacitor		
C4, C5:	AJ810		
C6:	1000pF Chip Capacitor		
C7:	0.01μF Disc Ceramic		
C8, C9:	1000pF Unelco		
C10:	10μF, 35V Electrolytic		
LI:	0.47μH Molded Choke		
L2:	2 Turns, #20 AWG, 1/8" I.D.		
L3	2 Turns in Ferroxcube VK200/19-4B		
Board Material:	3M-K6098, 1/16" Thick		

PACKAGE MECHANICAL

Table 8. M122 Mechanical Data

Symbol		millimeters		inches		
	Min	Тур	Max	Min	Тур	Max
А	25.65		26.80	1.010		1.055
В	5.59		5.84	0.220		0.230
С	6.86		7.24	0.270		0.285
D	0.08		0.18	0.003		0.007
Е	2.97		3.48	0.117		0.137
F		14.53			0.572	
G		3.30			0.130	
Н	6.22		6.48	0.245		0.255
I		16.26			0.640	
J	4.45		5.51	0.175		0.217
K	6.99		7.24	0.275	_	0.285

Figure 9. M122 Package Dimensions



Note: Drawing is not to scale.

REVISION HISTORY

Table 9. Revision History

Date	Revision	Description of Changes
November-1992	1	First Issue
28-May-2004	2	Stylesheet update. No content change.

Obsolete Product(s). Obsolete Product(s)

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